# HTN8G36S015P



15W, 3300 - 3600 MHz LDMOS Amplifier

Product datasheet

### **Description**

The HTN8G36S015P is an unmatched discrete LDMOS Power Amplifier with 15W saturated output power covering frequency range from 3300 - 3600 MHz.

#### **Features**

Operating Frequency Range: 3300 - 3600 MHz

• Operating Drain Voltage: +28V

Saturation Output Power: 15W

Power Average: 1.0W

 Excellent thermal stability due to low thermal resistance package

Enhanced robustness design without device degradation

• Efficiency: 13.1%@3450MHz, LTE

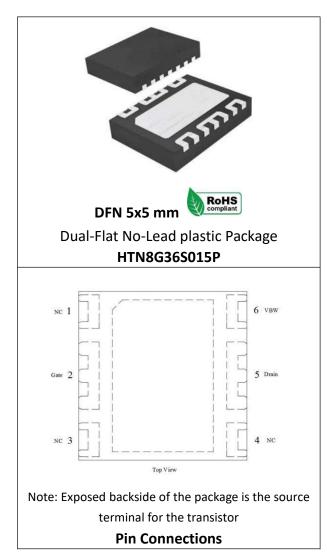
• Gain: 17.5dB@3450MHz, LTE

#### **Applications**

- mMIMO Driver stage
- Small Base station Final stage

#### **Ordering Information**

| Part Number     | Description         |
|-----------------|---------------------|
| HTN8G36S015P    | Reel Package        |
| HTN8G36S015PEVB | 3300 - 3600 MHz EVB |





Product datasheet

## **Typical Performance**

#### **RF Characteristics (LTE)**

| Freq (MHz) | MHz) Gain (dB) Eff (%) |      | ACPR (dBc)* |
|------------|------------------------|------|-------------|
| 3450       | 17.5                   | 13.1 | -47.4       |

Test conditions unless otherwise noted: 25 °C, VDD = +28Vdc, PAVG = 30~dBm (1W), FDD LTE 20MHz DL Signal, 9.6 dB PAR @ 0.01% CCDF test on HOTLO Application Board

### **Absolute Maximum Ratings**

| Parameter                              | Range/Value | Unit |
|--|-------------|------|
| Drain voltage (VDSS)                   | -0.5 to +65 | V    |
| Gate voltage (VGS)                     | -6 to +10   | V    |
| Drain voltage (VDD)                    | 0 to +32    | V    |
| Storage Temperature (Tstg)             | -65 to +150 | °C   |
| Junction Temperature (T <sub>J</sub> ) | -40 to +225 | °C   |

## **Electrical Specification**

#### **DC Characteristics (Main)**

| Parameter                   | Conditions        | Min | Тур | Max | Unit |
|-----------------------------|-------------------|-----|-----|-----|------|
| Breakdown Voltage V(BR)DSS  | Vgs=0V, Ids=17uA  | 65  | -   | -   | V    |
| Gate-Source Threshold       | \/ac-\/dc  dc-17\ |     | 1 [ |     | V    |
| Voltage V <sub>GS(th)</sub> | Vgs=Vds, Ids=17uA | -   | 1.5 | -   | V    |
| Drain Leakage Current IDSS1 | Vgs=0V, Vds=65V   | -   | -   | 500 | nA   |
| Drain Leakage Current IDSS2 | Vgs=0V, Vds=28V   | -   | -   | 100 | nA   |
| Gate Leakage Current IGSS1  | Vgs=0V, Vds=10V   | -   | -   | 1   | uA   |
| Gate Leakage Current IGSS2  | Vgs=0V, Vds=-6V   | -   | -   | 200 | uA   |

<sup>\*</sup>Uncorrected DPD



Product datasheet

#### **DC Characteristics**

| Parameter                   | Conditions           | Min | Тур | Max | Unit |
|-----------------------------|----------------------|-----|-----|-----|------|
| Breakdown Voltage V(BR)DSS  | Vgs=0V, Ids=17uA     | 65  | -   | -   | V    |
| Gate-Source Threshold       | \/ds_10\/ \ ds_17\\\ | 1.3 | -   | 1.7 | V    |
| Voltage V <sub>GS(th)</sub> | Vds=10V, Ids=17uA    |     |     |     | V    |
| Drain Leakage Current IDSS1 | Vgs=0V, Vds=65V      | -   | -   | 500 | nA   |
| Drain Leakage Current IDSS2 | Vgs=0V, Vds=28V      | -   | -   | 100 | nA   |
| Gate Leakage Current IGSS1  | Vgs=5V, Vds=5V       | -   | -   | 10  | nA   |
| Gate Leakage Current IGSS2  | Vgs=10V, Vds=0V      | -   | -   | 500 | nA   |

#### **Load Mismatch Test**

| Condition   | Test Result |
|---|-------------|
| VSWR=10:1, at all Phase Angles, VDD = +28Vdc, Pout = 30 dBm | No Device   |
| NR-100MHz @3450 MHz test on HOTLO Application Board         | Degradation |

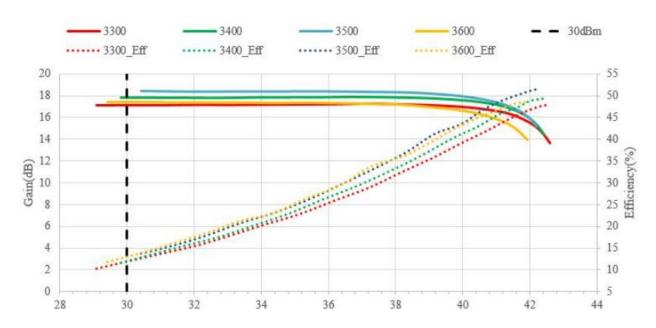
#### **Thermal Information**

| Parameter Condition    |                        | Value (Typ) | Unit  |
|------------------------|------------------------|-------------|-------|
| Thermal Resistance     | Tcase= 50°C, CW 15W    | 2 5         | °C /W |
| Junction to Case (Rтн) | TCASE - 30 C, CVV 13VV | 2.5         | C/W   |

# 15W, 3300 - 3600 MHz LDMOS Amplifier

Product datasheet

### Performance Plots 3300 - 3600 MHz Reference Design



Pulsed CW, Gain and Efficiency vs Pout

| Freq (MHz) | Gain (dB) | P1dB (dBm) | Eff(%)@P1dB | P3dB (dBm) | Eff(%)@P3dB |
|------------|-----------|------------|-------------|------------|-------------|
| 3300       | 17.24     | 41.44      | 44.76       | 42.46      | 47.74       |
| 3400       | 17.89     | 41.32      | 46.36       | 42.32      | 49.19       |
| 3500       | 18.43     | 40.94      | 47.89       | 42.15      | 51.25       |
| 3600       | 17.44     | 40.31      | 44.34       | 41.75      | 48.35       |

Test conditions unless otherwise noted: 25 °C, VDD = +28Vdc, IDQ= 180mA, PW = 1ms, DC= 10% test on HOTLO Application Board



# 15W, 3300 - 3600 MHz LDMOS Amplifier

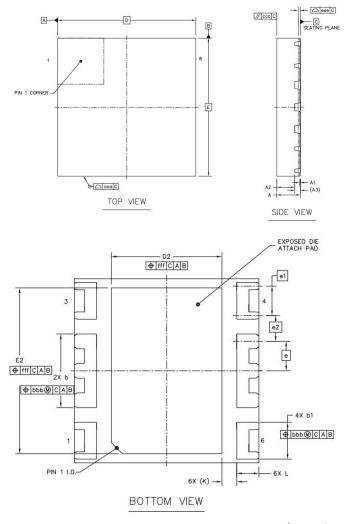
Product datasheet

### **Package Marking and Dimensions**



- Line1 (fixed): Device name in W/O
- Line2 (unfixed): Take the last 8 digits of Marking Lot No in W/O (Sample: E596-20140001, just take "20140001")
- Line3 (unfixed): Date Code + JY
  This Marking SPEC only stipulates the
  content of Marking. For marking
  requirements such as font and size,
  please refer to the latest version of
  "Holto Product Printing Specification"

#### Marking



|                     |          | SYMBOL | MIN       | NOM   | MAX  |
|---------------------|----------|--------|-----------|-------|------|
| TOTAL THICKNESS     |          | A      | 0.8       | 0.85  | 0.9  |
| STAND OFF           |          | A1     | 0         | 0.02  | 0.05 |
| MOLD THICKNESS      |          | A2     |           | 0.65  |      |
| L/F THICKNESS       |          | A3     | 0.203 REF |       |      |
| LEAD WEET           |          | b      | 1.95      | 2     | 2.05 |
| LEAD WIDTH          |          | b1     | 0.95      | 1     | 1.05 |
| BODY SIZE           | ×        | D      |           | 5 BSC |      |
| BODT SIZE           | Y        | E      |           | 5 BSC |      |
| LEAD PITCH          |          | e      | 0.8 BSC   |       |      |
|                     |          | e1     | 0.8 BSC   |       |      |
|                     |          | e2     | 0.7 BSC   |       |      |
| EP SIZE             | ×        | D2     | 2.9       | 3     | 3.1  |
| LF SIZE             | Y        | E2     | 4.4       | 4.5   | 4.6  |
| LEAD LENGTH         |          | L      | 0.5       | 0.6   | 0.7  |
| LEAD TIP TO EXPOSED | PAD EDGE | К      | 0.4 REF   |       |      |
| PACKAGE EDGE TOLERA | NCE      | aaa    | 0.1       |       |      |
| MOLD FLATNESS       |          | ccc    | 0.1       |       |      |
| COPLANARITY         |          | eee    | 0.08      |       |      |
| LEAD OFFSET         |          | bbb    | 0.1       |       |      |
| EXPOSED PAD OFFSET  |          | fff    | 0.1       |       |      |
|                     |          |        |           |       |      |
|                     |          |        |           |       |      |

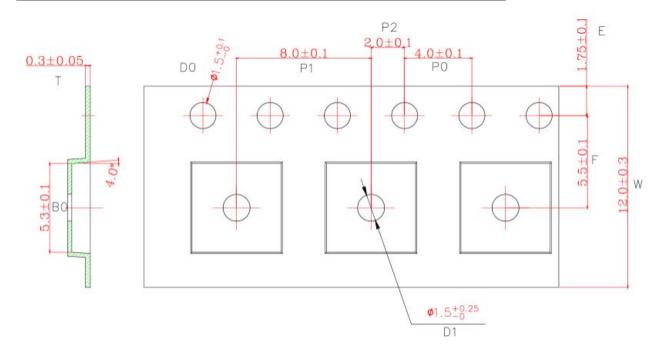
**Package Dimensions** 

# 15W, 3300 - 3600 MHz LDMOS Amplifier

Product datasheet

### **Tape and Reel Information**

| Package Type | Reel Size(inch) | Qty/Reel(pcs) | Qty/Box(pcs) | Qty/Carton(pcs) |
|--------------|-----------------|---------------|--------------|-----------------|
| DFN5*5       | 7inch           | 1000          | 8000         | 32000           |



**Tape & Reel Packaging Descriptions** 

### **Handling Precautions**

| Parameter                      | Grade |
|--------------------------------|-------|
| Moisture Sensitivity Level MSL | 3     |

| Parameter                        | Rating    | Standard        |
|----------------------------------|-----------|-----------------|
| ESD – Human Body Model (HBM)     | Class 1B  | JESD22-A114     |
| ESD – Human Body Model (MM)      | Class A   | EIA/JESD22-A115 |
| ESD – Charged Device Model (CDM) | Class III | JESD22-C101     |



### **RoHS Compliance**

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU.

#### **Datasheet Status**



Product datasheet

| Document status       | Product status    | Definition                                 |  |
|-----------------------|-------------------|--|--|
| Objective Datasheet   | Design simulation | Product objective specification            |  |
| Preliminary Datasheet | Customer sample   | Engineering samples and first test results |  |
| Product Datasheet     | Mass production   | Final product specification                |  |

### **Abbreviations**

| Acronym | Definition                                   |  |
|---------|--|--|
| LDMOS   | Laterally-Diffused Metal-Oxide Semiconductor |  |
| CW      | Continuous Waveform                          |  |



Product datasheet

# **Revision history**

| Document ID | Datasheet Status | Release Date | Revision Version                              |
|-------------|------------------|--------------|---|
| Rev 2.2     | Product          | March 2023   | New format based on English version datasheet |
| Rev 2.3     | Product          | January 2024 | Update POD and package information            |

# **HOLTO**

## HTN8G36S015P 15W, 3300 - 3600 MHz LDMOS Amplifier

Product datasheet

#### **Contact Information**

For the latest specifications, additional product information, worldwide sales and distribution locations and information about HOTLO:

• Web: <u>www.andesource.com</u>

• Email: andehk@andesource.com

For technical questions and application information:

• Email: andetech@andesource.com

#### **Important Notice**

Information in this document is believed to be accurate and reliable. However, HOTLO does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

"Typical" parameters are the average values expected by HOTLO in large quantities and are provided for information purposes only. All information and specifications contained herein are subject to change without notice and customers should obtain and verify the latest relevant information before placing orders for HOTLO products.

The information contained herein or any use of such information does not grant, explicitly or implicitly, to any party any patent rights, licenses, or any other intellectual property rights, whether with regard to such information itself or anything described by such information.

Applications that are described herein for any of these products are for illustrative purposes only. HOTLO makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification. Customers are responsible for the design and operation of their applications and products using HOTLO products, and HOTLO accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the HOTLO product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third-party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

HOTLO products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety- critical systems or equipment, nor in applications where failure or malfunction of a HOTLO product can reasonably be expected to result in personal injury, death or severe property or environmental damage. This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.